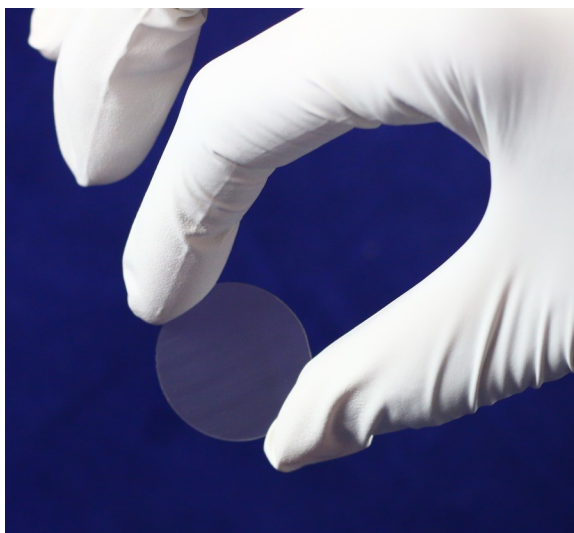


Crystalline β -Ga₂O₃ is a wide bandgap semiconductor (4.8-4.9 eV) which exhibits a high breakdown field of 8 MV/cm, high dielectric constant of 10 and electron mobility of >100 cm²/V-s. Kyma's (010) substrates are doped with iron to be semi-insulating for lateral device architectures. Kyma can also provide doped or undoped epilayers on these substrates.

Uses

- Basic research
- Deep ultraviolet (UV) photodetectors and high voltage power electronics



Orientation: (010) +/- 1°

Conduction Type: Semi-Insulating

Front Surface Finish: Epi-ready, RMS < 0.5 nm

Back Surface Finish: Optical polish

Edge Exclusion Area: 1mm

Available Sizes: 25.4 mm +/- 1 mm

Available Grades: Prime

Available Thickness: 450 μ m (\pm 50 μ m)

Typical XRD Linewidth of (020): <100 arcsec

*Other polishing options available: Double-side CMP, double-side optical
Other size, thickness, and offcut options available*